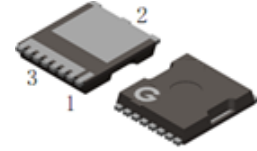
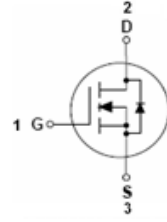


Features

- Advanced Shielded-Gate Trench technology
- Ultra-low on-resistance
- Low gate-charge
- HBM: JESD22-A114-B: 2
- RoHS compliant with Halogen-free

HF



TOLL

Mechanical Data

- Case: TOLL
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL008N06TH-TL	TOLL	2000 pcs / Tape & Reel	008N06TH

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	60	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Package Limited)	I _D	350	A
Continuous Drain Current (T _C = 25°C, Silicon Limited)		500	
Continuous Drain Current (T _C = 100°C, Silicon Limited)		350	
Continuous Drain Current (T _A = 25°C) ^{*1}		55	
Continuous Drain Current (T _A = 100°C) ^{*1}		39	
Pulsed Drain Current (t _p = 10μs, T _C = 25°C)	I _{DM}	2000	A
Single Pulse Avalanche Energy ^{*3}	E _{AS}	1500	mJ
Power Dissipation (T _C = 25°C)	P _D	428	W
Operating Junction Temperature Range	T _J	-55 ~ +175	°C
Storage Temperature Range	T _{STG}	-55 ~ +175	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	0.3	0.35	°C/W
Thermal Resistance Junction-to-Air ^{*1}	R _{θJA}	-	20	30	°C/W

Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance ^{*2}	$V_{GS} = 10V, I_D = 20A$	-	0.7	0.85	m Ω
		$V_{GS} = 6V, I_D = 20A$	-	0.9	1.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	2.5	4	V
R_G	Gate Resistance	$V_{GS} = 0V, f = 1MHz$	-	1.1	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V$	-	13000	-	pF
C_{OSS}	Output Capacitance	$V_{DS} = 30V$	-	3500	-	
C_{RSS}	Reverse Transfer Capacitance	$f = 100kHz$	-	230	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD} = 30V$	-	50	-	ns
t_r	Turn-on Rise Time	$V_{GS} = 15V$	-	99	-	
$t_{d(OFF)}$	Turn-Off Delay Time	$R_G = 3.3\Omega$	-	153	-	
t_f	Turn-Off Fall Time	$I_D = 20A$	-	26	-	
Q_G	Total Gate-Charge	$V_{DD} = 30V$	-	180	-	nC
Q_{GS}	Gate to Source Charge	$V_{GS} = 10V$	-	42	-	
Q_{GD}	Gate to Drain (Miller) Charge	$I_D = 20A$	-	32	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage ^{*2}	$I_S = 20A, V_{GS} = 0V$	-	0.75	1.2	V
t_{rr}	Reverse Recovery Time	$I_S = 20A, V_{GS} = 0V$	-	106	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100A/\mu s$	-	250	-	nC

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 40V, V_{GS} = 10V, L = 1mH$

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

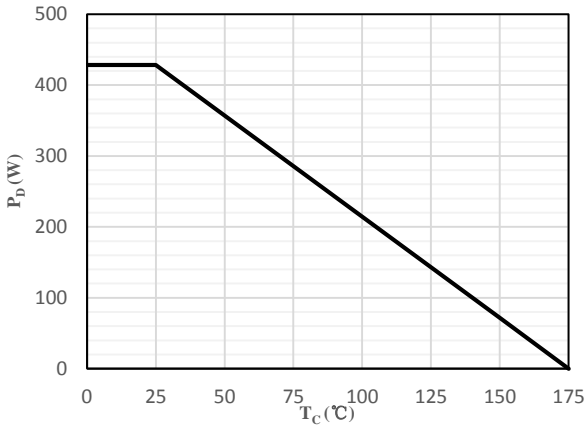


Fig 1 Power Dissipation

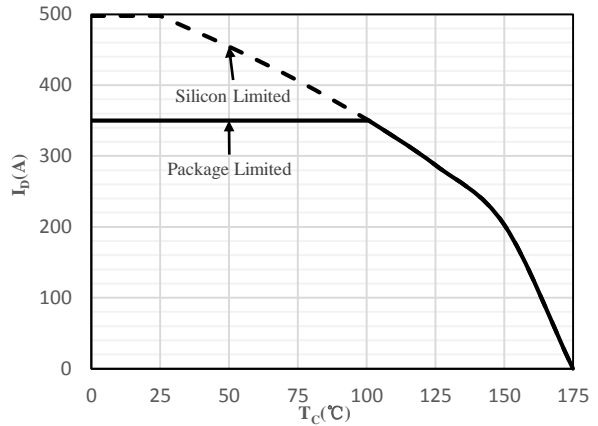


Fig 2 Drain Current

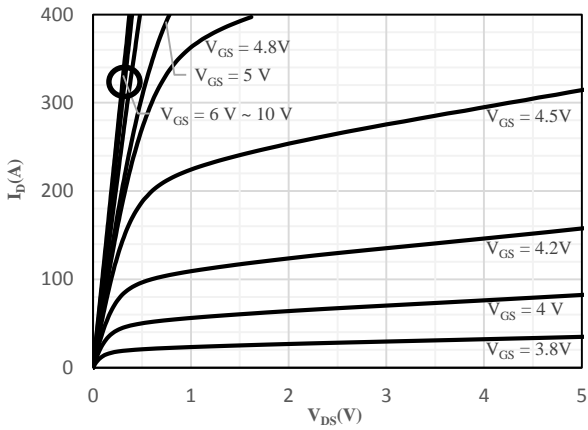


Fig 3 Typical Output Characteristics

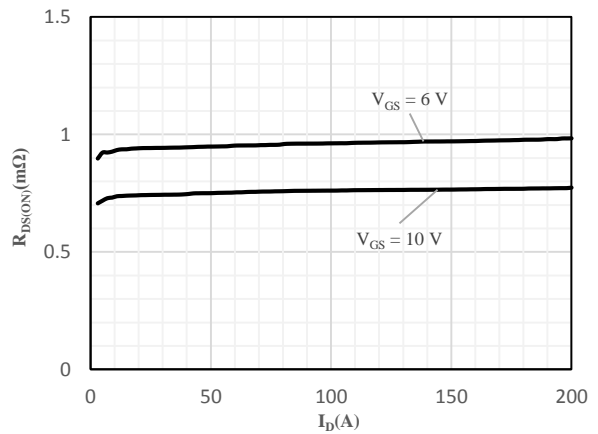


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

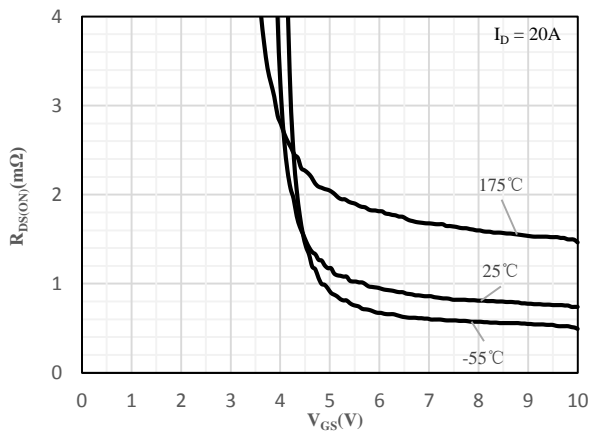


Fig 5 On-Resistance vs. Gate-Source Voltage

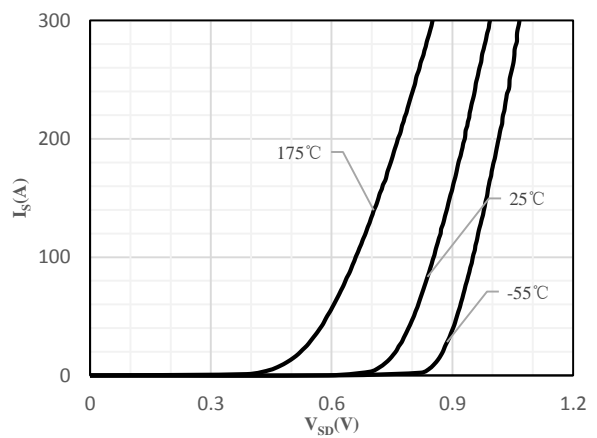


Fig 6 Body-Diode Characteristics

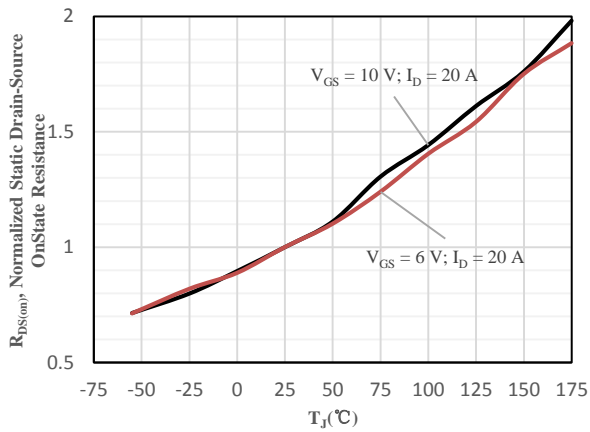


Fig 7 Normalized On-Resistance vs. Junction Temperature

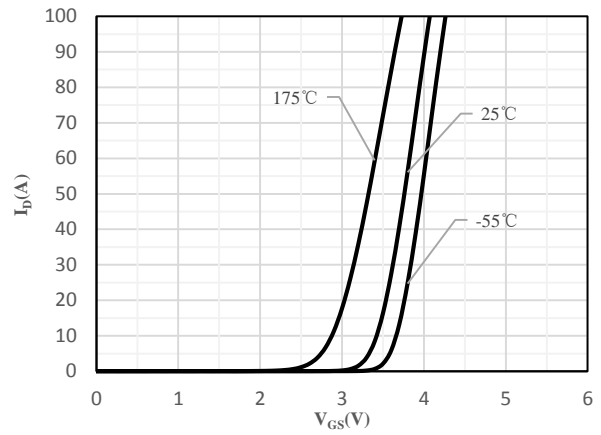


Fig 8 Transfer Characteristics

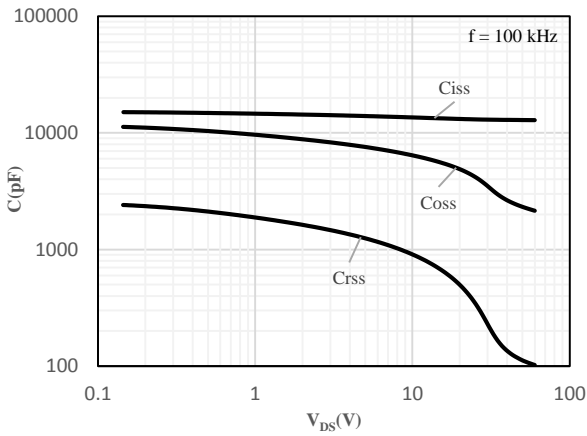


Fig 9 Capacitance Characteristics

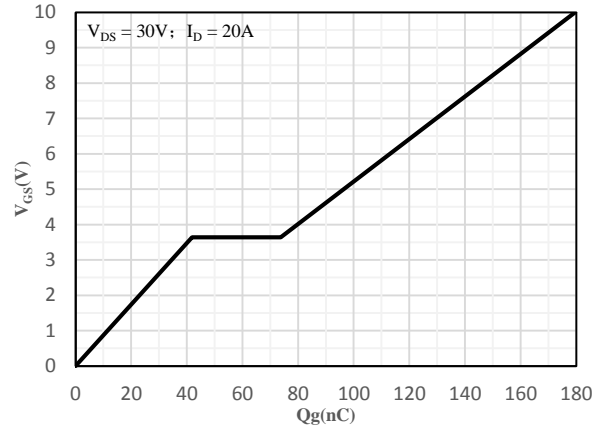


Fig 10 Gate-Charge Characteristics

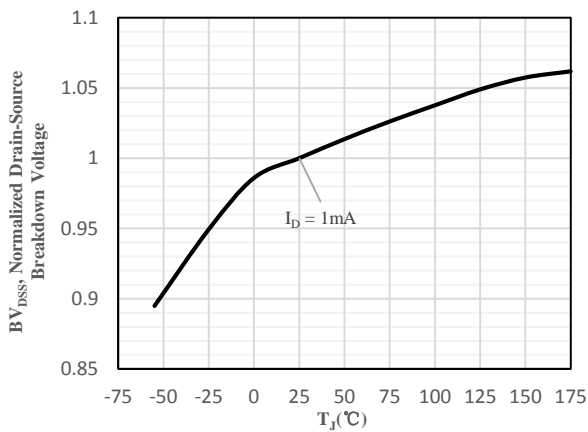


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

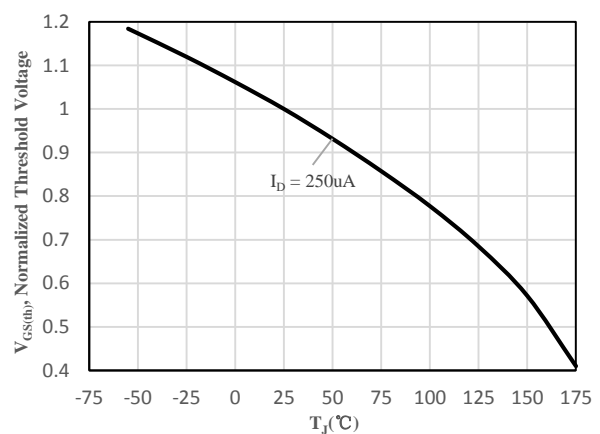


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

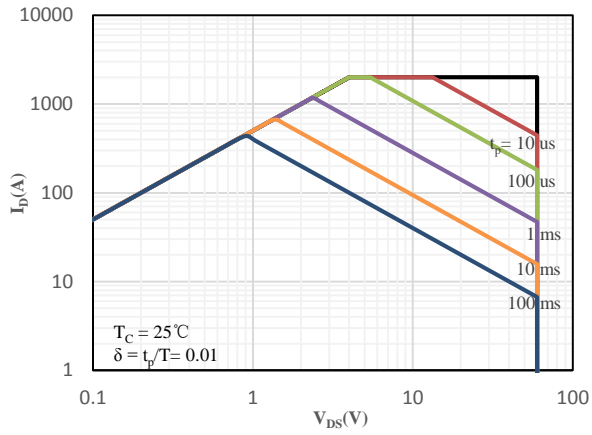


Fig 13 Safe Operating Area

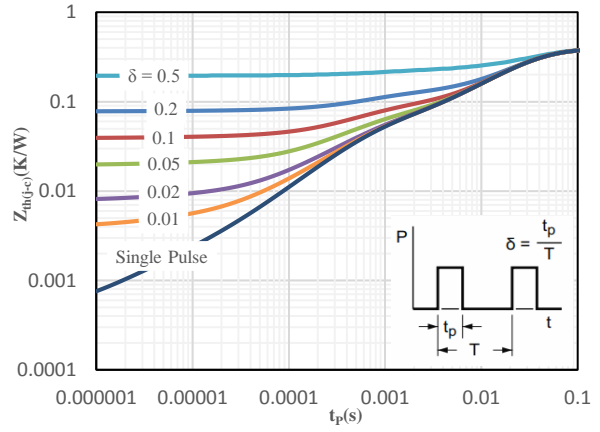
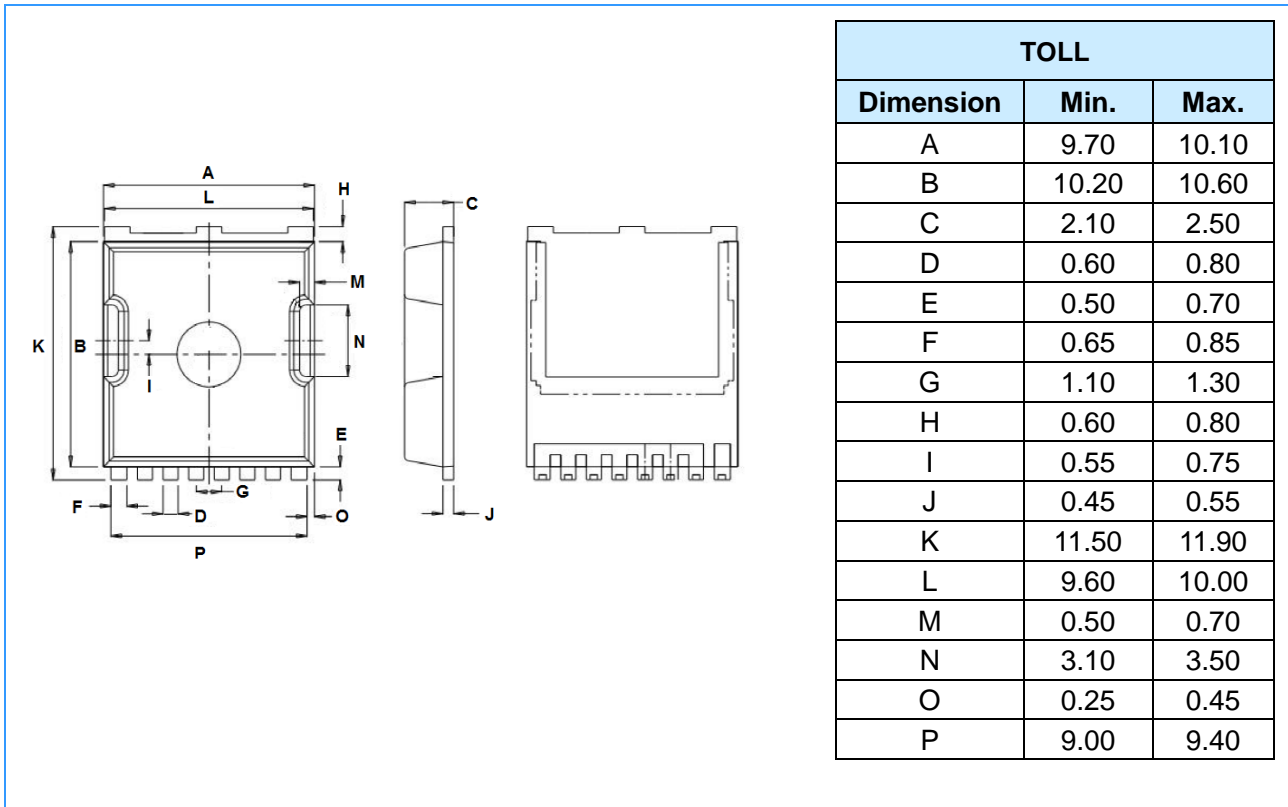


Fig 14 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



Soldering Footprint (Unit: mm)

